

What is an XBOD™ and what are its characteristics?

- Four layer silicon thyristor device that is triggered by a dV/dt pulse to the anode.
- Fast voltage fall times at <4 kV/device (<100 - 200 ns)
- Minimal insertion delay (<50 ns). This depends on the trigger pulse.
- Simple circular structure with no gates (inexpensive)
- Circular devices can be stacked in a conventional hermetic hockey-puck style package for realizing a high voltage (**20 kV**) switch
- Suitable for use in pulsed power applications requiring high action and high peak current switching

